

THE UNITED STATES PATENT AND TRADEMARK OFFICE

**REVOCATION AND NEW POWER OF ATTORNEY AND
CHANGE OF CORRESPONDENCE ADDRESS**

I, *Dr. Graham Fisher, Director of Intellectual Property of MEMC Electronic Materials, Inc.*, the Assignee of the entire right, title, and interest in the *U.S. Patent Application(s) and/or Patent(s) identified on the attached Schedule A*, hereby revoke all previous powers of attorney or authorizations of agent given and do hereby appoint the attorneys or agents associated with the following Customer Number, with full power of substitution and revocation, to prosecute and transact all business in the Patent and Trademark Office connected therewith for the *U.S. Patent Application(s) and/or Patent(s) listed in the attached Schedule A*:

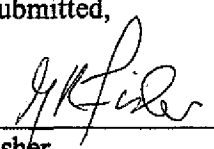
Customer Number: 76681

Please direct all correspondence in connection with said *U.S. Patent Application(s) and/or Patent(s)* to:

Customer Number: 76681

Respectfully submitted,

Date: 5/13/2008



Dr. Graham Fisher
Director of Intellectual Property
MEMC Electronic Materials, Inc.

PATENT

THE UNITED STATES PATENT AND TRADEMARK OFFICE

STATEMENT UNDER 37 CFR 3.73(b)

MEMC Electronic Materials, Inc., a Delaware Corporation, pursuant to 37 CFR 3.73(b), hereby states that it is the Assignee of the entire right, title, and interest in *U.S. Patent Application(s) and/or Patent(s) on the attached Schedule A.*

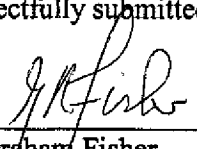
The entire rights, title, and interest in the aforementioned Patent Application(s) and/or Patent(s) were conveyed to **MEMC Electronic Materials, Inc.** via Assignment(s) recorded with the United States Patent and Trademark Office at the *Reel/Frame Numbers on the attached Schedule A.*

The undersigned, **Dr. Graham Fisher, Director of Intellectual Property**, has full authorization to act on behalf of Assignee **MEMC Electronic Materials, Inc.**

Respectfully submitted,

Date: _____

5/13/2008



Dr. Graham Fisher
Director of Intellectual Property
MEMC Electronic Materials, Inc.

APPENDIX A
Owned by MEMC Electronic Materials, Inc.

| ATTORNEY REFERENCE | CONF. NO | PUBLICATION NO. & DATE | SERIAL NO. FILING DATE | PATENT NO. ISSUE DATE | CURRENT OWNER/ ASSIGNEE | REEL AND FRAME NO. | TITLE |
|-------------------------|----------|---------------------------------|--------------------------|-------------------------|---------------------------------|--|---|
| MEMC2458.2 | 1268 | US-2003-0116081-A1 6/26/2003 | 10/260,239 9/30/2002 | 6,652,646 11/25/2003 | MEMC Electronic Materials, Inc. | Continuation of 09/853,232 which is a continuation of 09/344,036 recorded at 010481/0004 | PROCESS FOR GROWING A SILICON CRYSTAL SEGMENT SUBSTANTIALLY FREE FROM AGGLOMERATED INTRINSIC POINT DEFECTS WHICH ALLOWS FOR VARIABILITY IN THE PROCESS CONDITIONS |
| MEMC2462.1 | 7225 | US-2002-0086539-A1 7/14/2002 | 10/022,967 12/13/2001 | 7,008,874 3/7/2006 | MEMC Electronic Materials, Inc. | 012722/0205 | PROCESS FOR RECLAIMING SEMICONDUCTOR WAFERS AND RECLAIMED WAFERS |
| MEMC2464 | 5164 | US-2002-0004305-A1 1/10/2002 | 09/481,080 11/1/2000 | 6,376,395 4/23/2002 | MEMC Electronic Materials, Inc. | 010697/0282 | SEMICONDUCTOR WAFER MANUFACTURING PROCESS |
| MEMC2466.1 | 6579 | | 09/691,994 10/19/2000 | 6,503,322 1/7/2003 | MEMC Electronic Materials, Inc. | Division of 09/338,826 recorded at 010132/0716 | ELECTRICAL RESISTANCE HEATER AND METHOD FOR CRYSTAL GROWING APPARATUS |
| MEMC2471 | 9361 | US-2001-0008114-A1 7/19/2001 | 09/344,709 6/25/1999 | 6,328,795 12/11/2001 | MEMC Electronic Materials, Inc. | 010198/0955 | PROCESS FOR GROWTH OF DEFECT FREE SILICON CRYSTALS OF ARBITRARILY LARGE DIAMETERS |
| MEMC2471.1 | 4680 | US-2002-0092480-A1 7/18/2002 | 10/035,540 10/23/2001 | 6,562,123 5/13/2003 | MEMC Electronic Materials, Inc. | Continuation of 09/344,709 recorded at 010198/0955 | PROCESS FOR GROWING DEFECT-FREE SILICON WHEREIN THE GROWN SILICON IS COOLED IN A SEPARATE CHAMBER |
| MEMC2471.2 | 3364 | US-2004-0003770-A1 1/8/2004 | 10/437,141 5/13/2003 | 6,913,647 7/5/2005 | MEMC Electronic Materials, Inc. | Continuation of 10/035,540 which is a continuation of 09/344,709 recorded at 010198/0955 | PROCESS FOR COOLING A SILICON INGOT HAVING A VACANCY DOMINATED REGION TO PRODUCE DEFECT FREE SILICON |
| MEMC2477 | 8073 | | 09/358,616 7/19/1999 | 6,114,245 9/5/2000 | MEMC Electronic Materials, Inc. | Continuation of 08/915,975 recorded at 8681/0767 | METHOD OF PROCESSING SEMICONDUCTOR WAFERS |
| 28744-161 (MEMC2489) | 3575 | | 09/366,850 8/4/1999 | 6,828,690 12/7/2004 | MEMC Electronic Materials, Inc. | 010225/0266 | NON-UNIFORM MINORITY CARRIER LIFETIME DISTRIBUTIONS IN HIGH PERFORMANCE SILICON POWER DEVICES |
| MEMC2489.1 | 1211 | US2005-0006796 A1 1/13/2005 | 10/911,965 8/5/2004 | 7,242,037 7/10/2007 | MEMC Electronic Materials, Inc. | Division of 09/366,850 recorded at 010225/0266 | NON-UNIFORM MINORITY CARRIER LIFETIME DISTRIBUTION IN HIGH PERFORMANCE SILICON POWER DEVICES |
| MEMC2493 | 3777 | | 09/421,187 10/19/1999 | 6,203,611 3/20/2001 | MEMC Electronic Materials, Inc. | 010344/0075 | METHOD OF CONTROLLING GROWTH OF A SEMICONDUCTOR CRYSTAL TO AUTOMATICALLY TRANSITION FROM TAPER GROWTH TO TARGET DIAMETER GROWTH |
| MEMC2495 | 1207 | | 09/379,383 8/23/1999 | 6,336,968 1/8/2002 | MEMC Electronic Materials, Inc. | 010296/0838 | NON-OXYGEN PRECIPITATING CZOCHELSKI SILICON WAFERS |